

Hengze Qu

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5411481/publications.pdf>

Version: 2024-02-01

15
papers

316
citations

933447

10
h-index

996975

15
g-index

15
all docs

15
docs citations

15
times ranked

253
citing authors

#	ARTICLE	IF	CITATIONS
1	Designing sub-10-nm Metal-Oxide-Semiconductor Field-Effect Transistors via Ballistic Transport and Disparate Effective Mass: The Case of Two-Dimensional BiSb . <i>Physical Review Applied</i> , 2020, 13, .	3.8	69
2	Anisotropic In-plane Ballistic Transport in Monolayer Black Arsenic Phosphorus FETs. <i>Advanced Electronic Materials</i> , 2020, 6, 1901281.	5.1	59
3	Uncovering the Anisotropic Electronic Structure of 2D Group VA-VA Monolayers for Quantum Transport. <i>IEEE Electron Device Letters</i> , 2021, 42, 66-69.	3.9	31
4	Unusual Electronic Transitions in Two-dimensional Layered SnSb_2 Driven by Electronic State Rehybridization. <i>Physical Review Applied</i> , 2019, 11, .	3.8	21
5	Ultrascaled Double-Gate Monolayer SnS_2 MOSFETs for High-Performance and Low-Power Applications. <i>Physical Review Applied</i> , 2020, 14, .	3.8	21
6	Extending Channel Scaling Limit of p-MOSFETs Through Antimonene With Heavy Effective Mass and High Density of State. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 857-862.	3.0	17
7	Enhanced interband tunneling in two-dimensional tunneling transistors through anisotropic energy dispersion. <i>Physical Review B</i> , 2022, 105, .	3.2	16
8	High-Performance and Low-Power Transistors Based on Anisotropic Monolayer Te_2Se . <i>Physical Review Applied</i> , 2022, 17, .	3.8	15
9	Ballistic Quantum Transport of Sub-10 nm 2D $\text{Sb}_2\text{Te}_2\text{Se}$ Transistors. <i>Advanced Electronic Materials</i> , 2019, 5, 1900813.	5.1	14
10	Ballistic Transport in High-Performance and Low-Power Sub-5 nm Two-Dimensional ZrNBr MOSFETs. <i>IEEE Electron Device Letters</i> , 2020, 41, 1029-1032.	3.9	14
11	DFT coupled with NEGF study of the electronic properties and ballistic transport performances of 2D SbSiTe_3 . <i>Nanoscale</i> , 2020, 12, 9958-9963.	5.6	11
12	A Machine Learning Approach for Optimization of Channel Geometry and Source/Drain Doping Profile of Stacked Nanosheet Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 3568-3574.	3.0	10
13	Electronic structure and transport properties of 2D RhTeCl : a NEGF-DFT study. <i>Nanoscale</i> , 2019, 11, 20461-20466.	5.6	8
14	Quantum Transport in Monolayer CS Field-Effect Transistors. <i>Advanced Electronic Materials</i> , 2021, 7, 2001169.	5.1	6
15	First-principle study of puckered arsenene MOSFET. <i>Journal of Semiconductors</i> , 2020, 41, 082006.	3.7	4